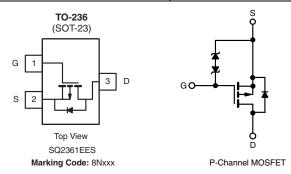


www.vishay.com

Vishay Siliconix

# Automotive P-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	- 60			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.150			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.200			
I <sub>D</sub> (A)	- 2.5			



### **FEATURES**

• TrenchFET® Power MOSFET

• Typical ESD Protection: 800 V

AEC-Q101 Qualified

• 100 % R<sub>q</sub> and UIS Tested

Material categorization:
For definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>





ROHS COMPLIANT HALOGEN FREE

ORDERING INFORMATION	
Package	SOT-23
Lead (Pb)-free and Halogen-free	SQ2361EES-T1-GE3

<b>ABSOLUTE MAXIMUM RATING</b>	<b>S</b> (T <sub>C</sub> = 25 °C, unless	s otherwise noted	(b)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		$V_{DS}$	- 60	
Gate-Source Voltage		V <sub>GS</sub>	± 20	V
Continuous Drain Current	T <sub>C</sub> = 25 °C	- I <sub>D</sub>	- 2.5	
	T <sub>C</sub> = 125 °C		- 1.4	
Continuous Source Current (Diode Conduction)		I <sub>S</sub>	- 2.5	Α
Pulsed Drain Current <sup>a</sup>		I <sub>DM</sub>	- 10	
Single Pulse Avalanche Current	1 0 1 1	I <sub>AS</sub>	- 15	
Single Pulse Avalanche Energy	L = 0.1 mH	E <sub>AS</sub>	11	mJ
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	D	2	W
	T <sub>C</sub> = 125 °C		0.67	
Operating Junction and Storage Temperatur	re Range	T <sub>J</sub> , T <sub>stq</sub>	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient P	CB Mount <sup>b</sup>	$R_{thJA}$	175	°C/W	
Junction-to-Foot (Drain)		$R_{thJF}$	75		

## Notes

- a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- b. When mounted on 1" square PCB (FR-4 material).

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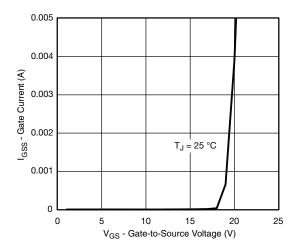
PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		- 60	-	-	V	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{GS}$ , $I_{D} = -250 \mu A$	- 1.5	-	- 2.5	]	
Gate-Source Leakage	l	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		1	-	± 30	mA	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$		-	± 2		
Zero Gate Voltage Drain Current		$V_{GS} = 0 V$	V <sub>DS</sub> = - 60 V	1	-	- 1	] ,,,	
	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = - 60 V, T <sub>J</sub> = 125 °C	1	-	- 50	- μA -	
		$V_{GS} = 0 V$	V <sub>DS</sub> = - 60 V, T <sub>J</sub> = 175 °C	-	-	- 150		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = - 10 V	$V_{DS} \le -5 V$	- 10	-	-	Α	
		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 2.4 A	-	0.115	0.150		
Drain-Source On-State Resistance <sup>a</sup>		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 2.4 A , T <sub>J</sub> = 125 °C	-	-	0.260		
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 2.4 A, T <sub>J</sub> = 175 °C	-	-	0.310	Ω	
		V <sub>GS</sub> = - 4.5 V	I <sub>D</sub> = - 1.8 A	-	0.160	0.200		
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> =	: - 10 V, I <sub>D</sub> = - 2 A	-	5	-	S	
Dynamic <sup>b</sup>								
Input Capacitance	C <sub>iss</sub>			-	435	545	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>GS</sub> = 0 V V <sub>DS</sub> = - 30 V, f = 1 MHz	-	55	70		
Reverse Transfer Capacitance	C <sub>rss</sub>			-	40	50		
Total Gate Charge <sup>c</sup>	Qg		V <sub>GS</sub> = - 10 V	-	11.2	17		
Gate-Source Charge <sup>c</sup>	$Q_{gs}$	V <sub>GS</sub> = - 10 V		-	1.6	-	nC	
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			-	3.2	-		
Gate Resistance	R <sub>g</sub>	f = 1 MHz		2.7	5.4	8.1	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	7	11		
Rise Time <sup>c</sup>	t <sub>r</sub>	V <sub>DD</sub> =	$V_{DD} = -30 \text{ V}, R_1 = 20 \Omega$		8	12	- ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong$ - 1.5 A, $V_{GEN} =$ - 10 V, $R_g =$ 1 $\Omega$		-	19	29		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	8	12		
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>							
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	- 10	Α	
Forward Voltage	$V_{SD}$	I <sub>F</sub> = - 1.5 A, V <sub>GS</sub> = 0 V		_	- 0.8	- 1.2	V	

### Notes

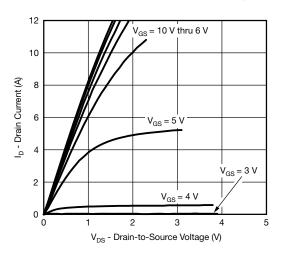
- a. Pulse test; pulse width  $\leq 300~\mu s,\,duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

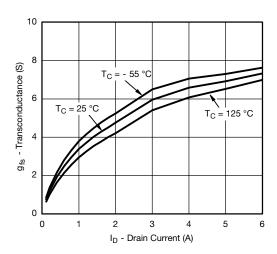
# TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



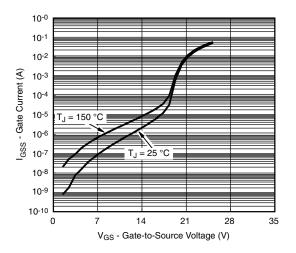
## Gate Current vs. Gate-Source Voltage



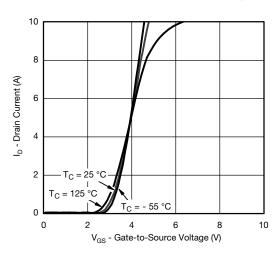
# **Output Characteristics**



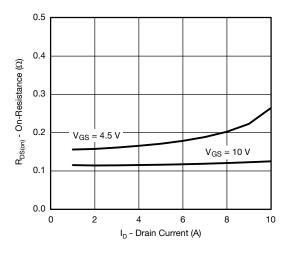
Transconductance



Gate Current vs. Gate-Source Voltage

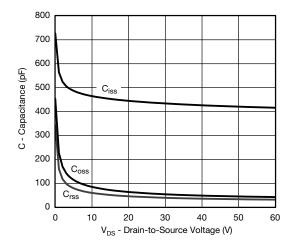


# **Transfer Characteristics**



On-Resistance vs. Drain Current

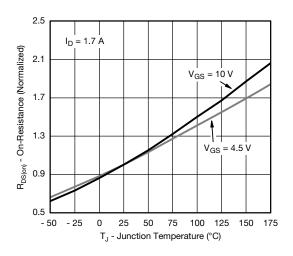
# TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



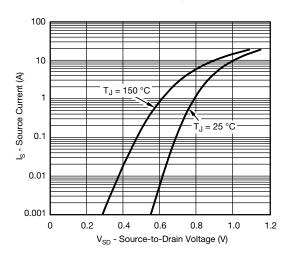
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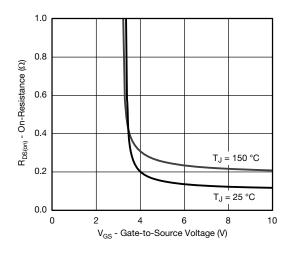
### Capacitance



Gate Charge

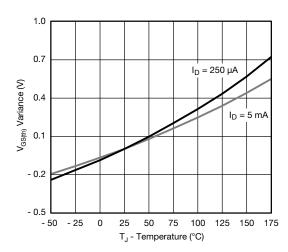


### On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-Source Voltage

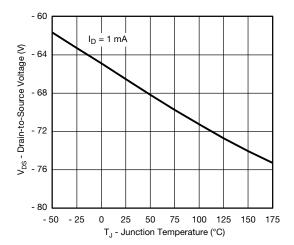
Source-Drain Diode Forward Voltage

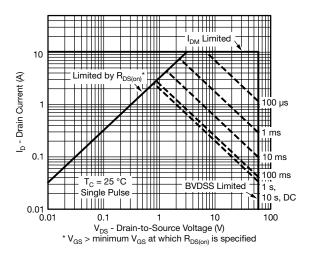


Threshold Voltage



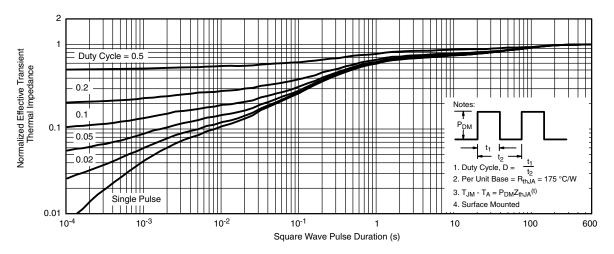
# **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)





Drain Source Breakdown vs. Junction Temperature

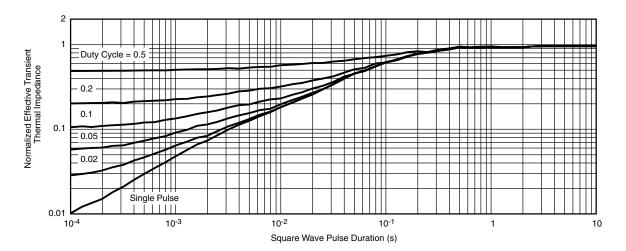
## Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



### Normalized Thermal Transient Impedance, Junction-to-Foot

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?70953">www.vishay.com/ppg?70953</a>.



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